

Supplementary Information

Homogeneity and tolerance to heat of monolayer MoS₂ on SiO₂ and h-BN

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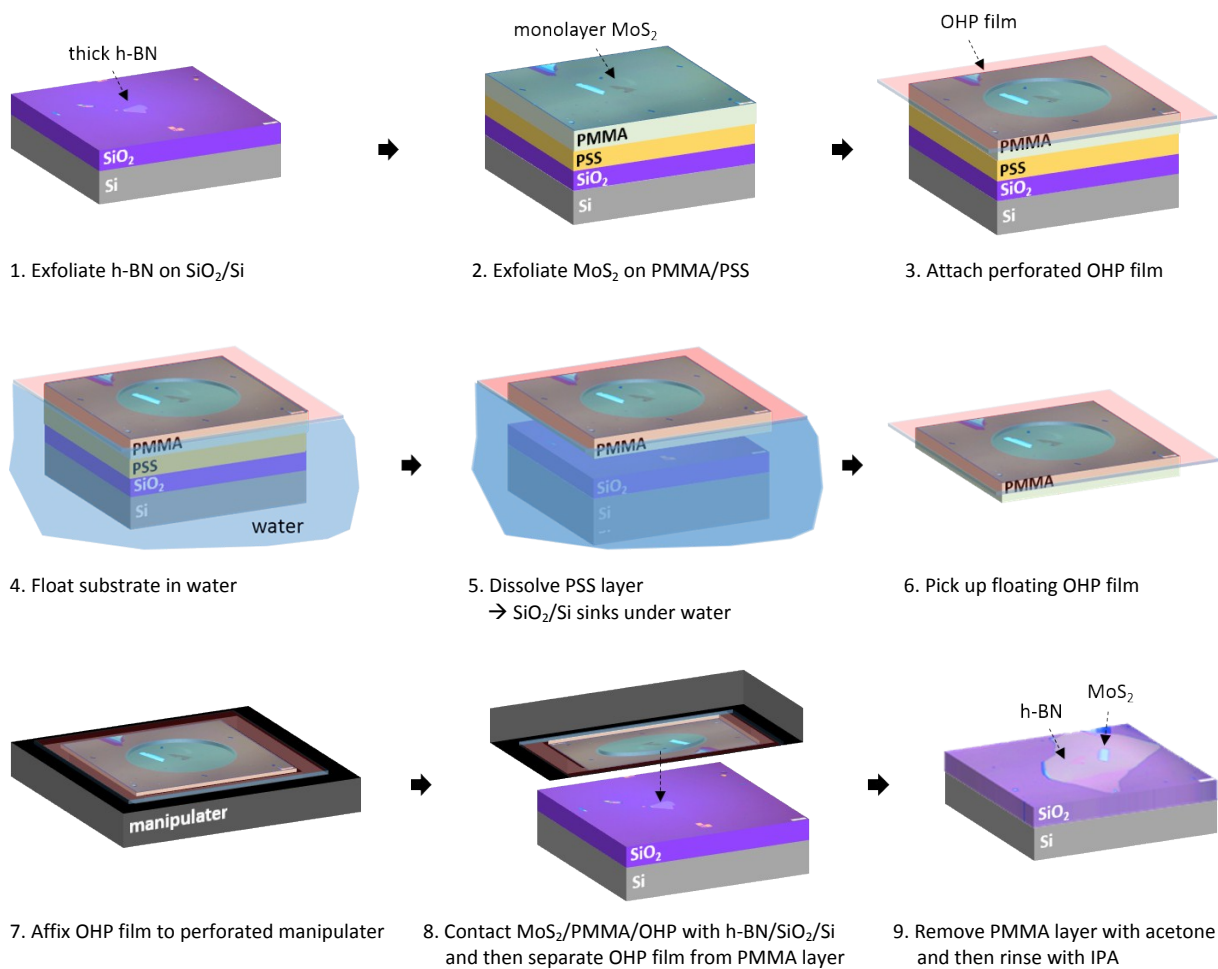
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* PMMA: poly(methyl methacrylate) / PSS: poly-styrenesulfonic / OHP: overhead projector / IPA: isopropyl alcohol

Fig. S1 Schematic diagram of the experimental process to fabricate MoS₂ and h-BN vertical heterostructures on SiO₂/Si substrate.